

ABSTRACT

A chemical amplification positive resist composition
5 comprising a polymeric mixture of a polyhydroxystyrene
derivative having a Mw of 1000-500,000 and a copolymer of
hydroxystyrene and (meth)acrylate having a Mw of 1000-
500,000, as a base resin, has improved dry etching
resistance, high sensitivity, high resolution, and process
10 adaptability, and is suppressed in the slimming of pattern
films after development with aqueous base.

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